

Effects of O₂ and N₂ atmospheres on the PTCR characteristics of Y-doped PTCR BaTiO₃ ceramics

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The positive temperature coefficient of resistivity (PTCR) materials in the perovskite-type ferroelectric consist of semiconducting barium titanate and its solid solutions with strontium titanate and lead titanate [1–6]. The PTCR BaTiO₃ ceramics sintered in air or oxidizing atmosphere exhibit an anomalous increase in electrical resistivity near the ferroelectric Curie temperature (~120 °C) [7–11]. PTCR characteristics of the semiconducting BaTiO₃ ceramics originate from the existence of an electrical potential barrier arising from the presence of a two-dimensional surface layer of acceptor state, e.g., segregated acceptor ions or adsorbed oxygen at the grain boundaries [8, 9, 12, 13]. PTCR characteristics of the semiconducting BaTiO₃ ceramics, annealed under vacuum or in reducing gas atmospheres, undergo changes that critically reduce the magnitude of the resistivity jump [14].

Porous PTCR BaTiO₃ ceramics has been reported to exhibit large PTCR effects [15–18]. Oxygen can adsorb at the grain boundaries because of the presence of pores in the porous ceramics, which are more favorable to form surface acceptor states compared with ordinary dense ceramics [19]. In this study, the porous PTCR BaTiO₃ ceramics are prepared by adding polyethylene glycol (PEG; 20 wt%). The aim of this study is to investigate the effect of measuring atmosphere (O₂, N₂) on the PTCR characteristics of the porous PTCR BaTiO₃ ceramics and to confirm the role of oxygen on the grain boundaries in origin of the PTCR characteristics of the porous ceramics.

High-purity PTCR BaTiO₃ ceramic powder was utilized in this study (Toho Titanium Co. Ltd, Japan). The powder was commercially obtained as BaTiO₃ powder containing SrTiO₃ (19.2 mol%) and Y₂O₃ (0.2 mol%). The powder is referred to as Y-doped BaTiO₃. The mean particle size and ferroelectric Curie temperature of the powder were 0.7 μm and 61 °C, respectively. The PEG (powder form, mean particle size: 50 μm, Shinyo Pure Chemicals Co. Ltd, Japan) of 20 wt% was added to the Y-doped BaTiO₃ powder and then mixed in a mortar for 1 h. The mixture was compacted by die-pressing at a pressure of 40 MPa to prepare the green compacts (15 × 12 × 7 mm³). The green compacts were sintered at 1350 °C for 1 h in air.

The microstructure of the Y-doped BaTiO₃ ceramics was analyzed by scanning electron microscopy (SEM). The average grain size of the ceramics was estimated by the line-intersecting method. During heating and cooling cycles in the temperature range of 25 to 300 °C, the electrical resistance was measured with a digital

multimeter under O₂ and N₂ atmospheres, and under N₂ followed by O₂ atmosphere.

Fig. 1 shows a SEM micrograph of the fractured Y-doped BaTiO₃ surfaces. It was found that the Y-doped BaTiO₃ ceramics containing PEG of 20 wt% had a high porosity (25.2%) and fine grain size (5.1 μm). The porous ceramic is advantageous to oxidize grain boundaries and to produce surface acceptor states [19]. The Y-doped BaTiO₃ ceramics was heated from 25 to 300 °C followed by cooling from 300 to 25 °C, in order to investigate how the adsorption or desorption of oxygen at the grain boundaries affects the magnitude of the PTCR effect during heating and cooling cycles.

Figs 2 and 3 show the electrical resistivities of the porous ceramics measured in O₂ and N₂ atmospheres, respectively, during heating and cooling cycles. The PTCR characteristics up to ~150 °C under O₂ and N₂ atmospheres are nearly same during heating, whereas those at high temperatures (>150 °C) are sensitive to the atmosphere. In O₂ atmosphere, the resistivity of the porous ceramics during cooling is slightly higher than that during heating cycle. This is due to a small increase in potential barrier because of a small decrease in the number of conduction electrons, owing to the adsorption of oxygen at the grain boundaries [20]. In N₂ atmosphere, the PTCR characteristics of the porous ceramics during cooling cycle are quite different from that during heating cycle. The resistivity of the porous ceramics during cooling is much lower than that during heating [21]. The magnitude of PTCR jump in the porous ceramics during cooling is low in comparison to

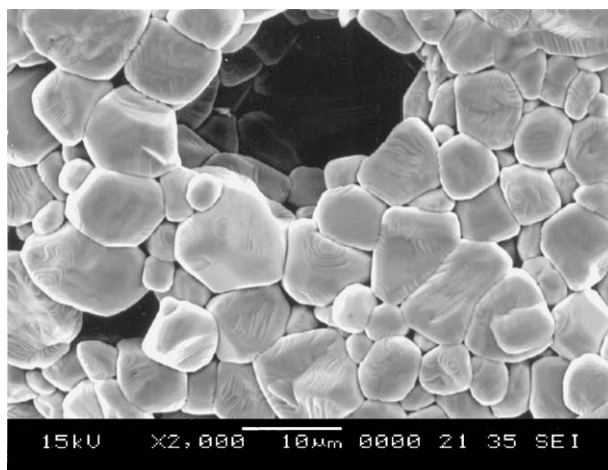


Figure 1 SEM micrograph of the fractured Y-doped BaTiO₃ surfaces.

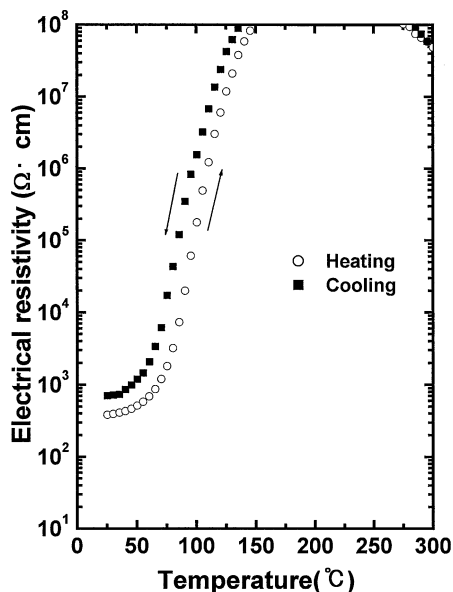


Figure 2 Electrical resistivities of the Y-doped BaTiO₃ ceramics measured during heating and cooling in O₂ atmosphere.

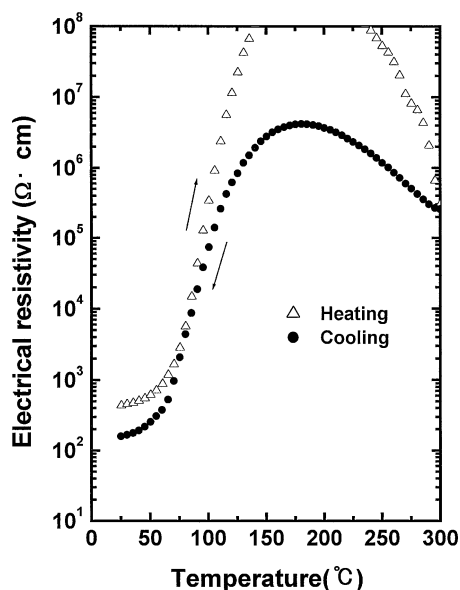


Figure 3 Electrical resistivities of the Y-doped BaTiO₃ ceramics measured during heating and cooling in N₂ atmosphere.

that during heating. The temperature corresponding to maximum resistivity during cooling is shifted to lower temperature.

Fig. 4 shows the electrical resistivity of the porous ceramics during heating and cooling cycles, when the atmosphere was changed from the reducing N₂ to O₂ atmosphere. It is confirmed that the low-temperature resistivity of the porous ceramics is found to be lowered during cooling after heating in N₂ atmosphere, and the resistivity is raised again by exposing to O₂ atmosphere. From this result, it is found that oxygen is adsorbed at the grain boundaries during heating in O₂ atmosphere, thus annihilating the oxygen vacancies created during N₂ reduction and significantly increasing the grain boundary resistance. These results con-

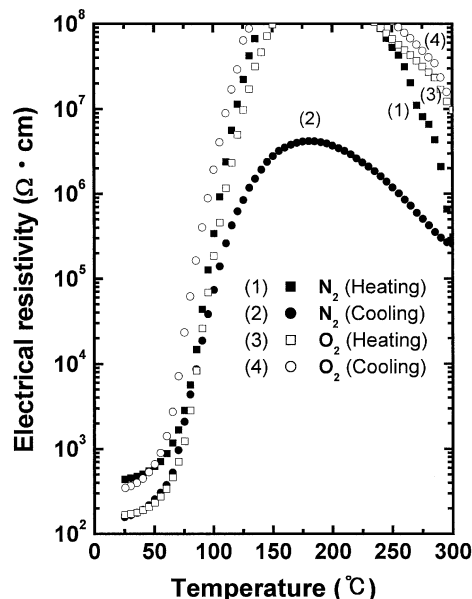


Figure 4 Electrical resistivity as a function of temperature of the Y-doped BaTiO₃ ceramics during heating and cooling. Atmosphere was changed from the reducing N₂ (■, ●) to O₂ (□, ○) atmosphere.

firm that the PTCR properties are strongly affected by chemisorbed oxygen at the grain boundaries and are recovered as the atmosphere is changed from reducing to oxidizing. The present study strongly supports the validity of the Heywang model [8, 12, 13].

References

1. H. NAGAMOTO, H. KAGOTANI and T. OKUBO, *J. Amer. Ceram. Soc.* **76** (1993) 2053.
2. H. EMOTO and J. HOJO, *J. Ceram. Soc. Jpn.* **100** (1992) 555.
3. I. C. HO, *J. Amer. Ceram. Soc.* **77** (1994) 829.
4. I. C. HO and H. L. HSIEH, *ibid.* **76** (1993) 2385.
5. H. F. CHENG, T. F. LIN and C. T. HU, *ibid.* **76** (1993) 827.
6. B. C. LACOURSE and V. R. W. AMARAKOON, *ibid.* **78** (1995) 3352.
7. O. SABURI, *J. Phys. Soc. Jpn.* **14** (1959) 1159.
8. W. HEYWANG, *J. Mater. Sci.* **6** (1971) 1214.
9. G. H. JONKER, *Solid State Electron.* **7** (1964) 895.
10. J. DANIELS and R. WERNIKE, *Philips Res. Rep.* **31** (1976) 544.
11. T. R. N. KUTTY, P. MURUGARAJ and N. S. GAJBHIYE, *Mater. Res. Bull.* **20** (1985) 565.
12. W. HEYWANG, *J. Amer. Ceram. Soc.* **47** (1964) 484.
13. W. HEYWANG, *Solid State Electron.* **3** (1961) 51.
14. M. KAHN, *Amer. Ceram. Soc. Bull.* **50** (1971) 676.
15. M. KUWABARA, *J. Amer. Ceram. Soc.* **64** (1981) 639.
16. S.-M. SU, L.-Y. ZHANG, H.-T. SUN and X. YAO, *ibid.* **77** (1994) 2154.
17. T. R. SHROUT, D. MOFFATT and W. HUEBNER, *J. Mater. Sci.* **26** (1991) 145.
18. J.-G. KIM, W.-S. CHO and K. PARK, *Mater. Sci. Eng. B* **77** (2000) 255.
19. M. KUWABARA, *Sol. State Elect.* **27** (1984) 929.
20. J. G. FAGAN and V. R. W. AMARAKOON, *Am. Ceram. Soc. Bull.* **72** (1993) 69.
21. H. ALLAK, G. RUSSEL and J. WOODS, *J. Phys. D. Appl. Phys.* **20** (1987) 1645.

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